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2N6548
 2N6549

NPN SILICON DARLINGTON TRANSISTORS

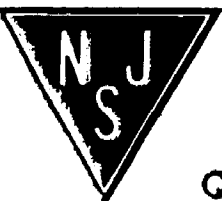
TO-202 CASE

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

	SYMBOL		UNIT
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CES}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	12	V
Collector Current	I _C	2.0	A
Base Current	I _B	100	mA
Power Dissipation	P _D	2.0	W
Power Dissipation (T _C =25°C)	P _D	10	W
Operating and Storage Junction Temperature	T _J , T _{STG}	-65 TO +150	°C
Thermal Resistance	θ _{JA}	62.5	°C/W
Thermal Resistance	θ _{JC}	12.5	°C/W

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N6548		2N6549		UNIT
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =30V		100		100	nA
I _{EBO}	V _{EB} =10V		100		100	nA
V _{CB0}	I _C =100μA	50		50		V
V _{CES}	I _C =100μA	40		40		V
V _{EBO}	I _E =10μA	12		12		V
V _{CE(SAT)}	I _C =1.0A, I _B =2.0mA		1.5		1.5	V
V _{CE(SAT)}	I _C =2.0A, I _B =4.0mA		2.0		2.0	V
V _{BE(SAT)}	I _C =1.0A, I _B =2.0mA		2.0		2.0	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =1.0A		2.0		2.0	V
h _{FE}	V _{CE} =5.0V, I _C =200mA	25,000	150,000	15,000	150,000	
h _{FE}	V _{CE} =5.0V, I _C =500mA	15,000		10,000		
h _{FE}	V _{CE} =5.0V, I _C =1.0A	5,000		3,000		
h _{fe}	V _{CE} =5.0V, I _C =50mA, f=1.0kHz	20,000		15,000		
f _T	V _{CE} =5.0V, I _C =200mA, f=100MHz	100		100		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		7.0		7.0	pF



NJ Semi-Conductors reserves the right to change test conditions, parameters limits and package dimensions without notice information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors